



100V 175°C NPN LOW SAT MEDIUM POWER TRANSISTOR IN POWERDI5060-8

Features

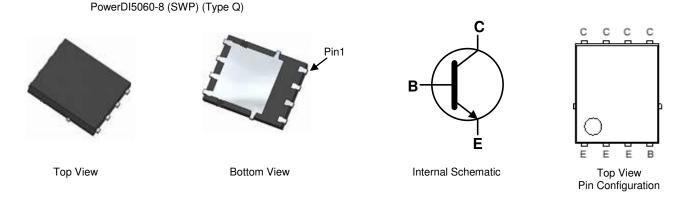
- BV_{CEO} > 100V
- I_C = 3A Continuous Collector Current
- I_{CM} = 6A Peak Pulse Current
- R_{CE(SAT)} <150mΩ
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTN3C100PSQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: PowerDl[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed Over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

Applications

- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- Backlighting Applications



Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN3C100PSQ-13	Automotive	DXTN3C100PS	13	12	2500

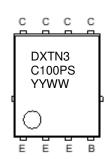
EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



DXTN3 = Product Type Marking Code C100PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated. DXTN3C100PSQ Document number: DS39305 Rev.2 - 2

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Base Current	IB	500	mA
Continuous Collector Current	lc	3	А
Peak Pulse Collector Current	I _{СМ}	6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	PD	2.5	W	
Thermal Registeres, Junction to Ambient	(Note 5)	D	60	°C 111	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	140	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	R _{0JL}	5.7	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

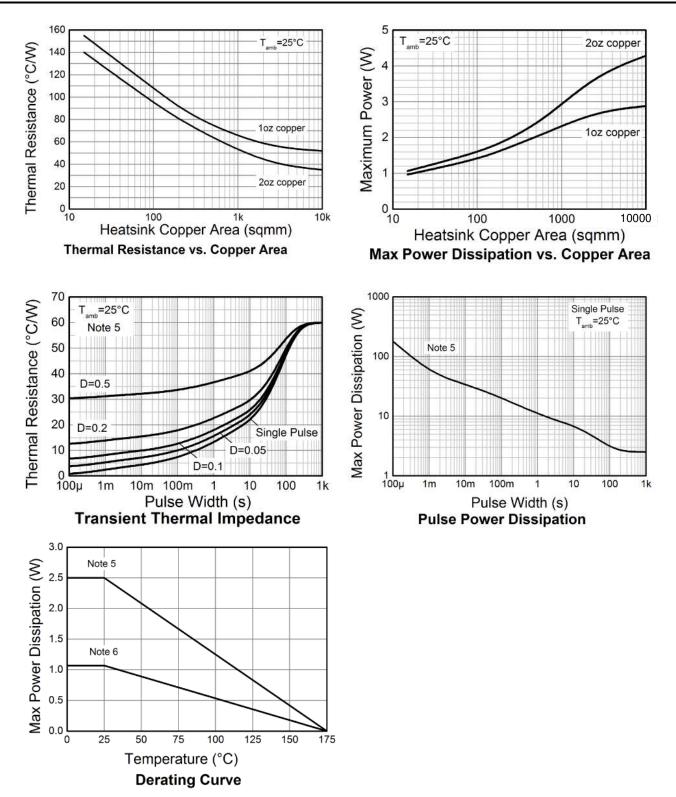
Notes: 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is

measured under still air conditions whilst operating in a steady-state.

Same as note (5), except mounted on minimum recommended pad layout.
Thermal resistance from junction to solder point (at the collector tab).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)





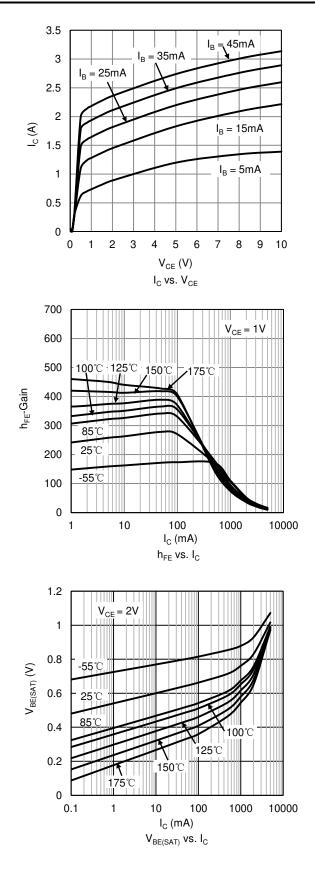
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

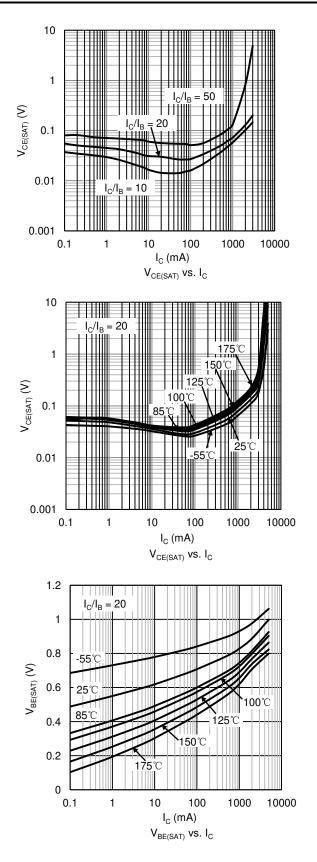
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	100	_	—	V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	100	_	—	V	I _C = 10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	—	V	I _E = 100μA	
Collector-Base Cutoff Current	1	—	_	100	nA	V _{CB} = 80V	
Collector-Base Cuton Current	I _{CBO}	_	—	50	μA	$V_{CB} = 80V @ T_{J} = +150^{\circ}C$	
Emitter Cutoff Current	I _{EBO}	_	—	100	nA	V _{EB} = 7V	
Collector-Emitter Cutoff Current	I _{CES}	—	_	100	nA	$V_{CES} = 80V$	
ON CHARACTERISTICS (Note 9)			-		-	-	
		150	250			$I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}$	
DC Current Gain		80	250	—		$I_{C} = 1A, V_{CE} = 10V$	
	hFE	20	100	—		$I_C = 2A, V_{CE} = 10V$	
		10	40	—		$I_{C} = 3A, V_{CE} = 10V$	
Collector Emitter Seturation Voltage		_	90	150	mV	$I_{C} = 1A, I_{B} = 50mA$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	225	330	mV	$I_{C} = 3A, I_{B} = 300mA$	
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	90	150	mΩ	$I_{C} = 1A, I_{B} = 50mA$	
Base Emitter Caturation Voltage	V	_	0.86	1.0	v	$I_{C} = 1A, I_{B} = 50mA$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1.0	1.2	v	$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$	
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.67	0.85	V	I _C = 0.1A, V _{CE} = 2V	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f _T	_	140	—	MHz	$V_{CE} = 10V, I_C = 100mA, f = 100MHz$	
Output Capacitance	Cobo	_	11	_	pF	V _{CB} = 10V, f = 1MHz	
Delay Time	t _d	_	20	_	ns		
Rise Time	tr	_	300	_	ns		
Turn-On Time	t _(on)	_	320	—	ns	V _{CC} = 12.5V, I _C = 1A	
Storage Time	ts	_	830	_	ns	$I_{B1} = -I_{B2} = 0.05A$	
Fall Time	t _f	_	470		ns		
Turn-Off Time	t _(off)	—	1300	_	ns]	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 $\mu s.$ Duty cycle \leq 2%.



Electrical Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)







PowerDI5060-8 (SWP) (Type Q) Min

0.90

0

0.30

0.20

4.70

3.56

3.46

1.05

10°

6°

Dim

Α

A1

b

b2

b4

С D

D1

D2

D2a

Ε

E1

E2

E2a

е

k

L

La

L1

L1a

L4

Μ

θ

θ1

Max

1.10

0.05

0.50

0.35

0.25REF

5.15 BS

5.10

3.96

6.40 BSC

3.86

0.230 0.330

3.78 4.18

5.60 6.00

4.195 4.595 1.27BSC

0.635 0.835

0.635 0.835

0.200 0.400

0.025 0.225

3.205 4.005

All Dimensions in mm

0.050RE

12°

8°

Тур

1.00

0.41

0.25

0.277

4.90

3.76

3.98

5.80

3.66

4.395

0.735

0.735

0.300

0.125

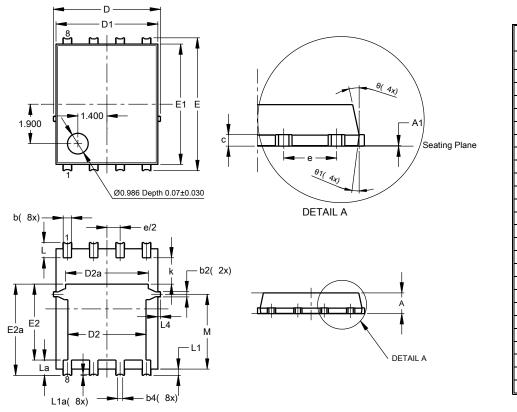
3.605

11°

7°

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

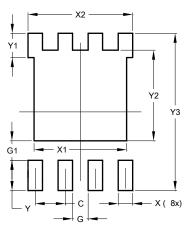


PowerDI5060-8 (SWP) (Type Q)

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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